## Abstract Submitted for the MAR06 Meeting of The American Physical Society

Shot noise in Cr-doped and undoped Co/Al<sub>2</sub>O<sub>3</sub>/Py magnetic tunnel junctions FARKHAD ALIEV, RUBEN GUERRERO, Departamento de Física de la Materia Condensada, C-III, Universidad Autónoma de Madrid, Cantoblanco, 28049, Madrid, Spain, PATRICK LE CLAIR², JAGADEESH MOODERA, Massachusetts Institute of Technology, Massachusetts 02139, USA — We have found that shot noise in Co(80Å) /Al<sub>2</sub>O<sub>3</sub>(14Å)/Py(100Å) magnetic tunnel junctions (MTJs) is reduced with respect to Poisonian value. The Fano factor, obtained at frequencies (100<f<1000Hz), temperatures (T<10K) and biases (below 150 meV) where the shot noise dominates, varies between F  $\approx$ 0.8 and 0.65, indicating correlated electron tunnelling. Doping of the insulating barrier with Cr inclusions suppresses the conductivity and tunnelling magnetoresistance, and restores the Fano factor to a value corresponding to uncorrelated transport (F $\approx$ 1). These results indicate an enhanced cross-correlation between electrons due to trapping or spin- flip assisted tunnelling in the undopped MTJs, and a possible Coulomb blockade in the Cr doped MTJs.

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